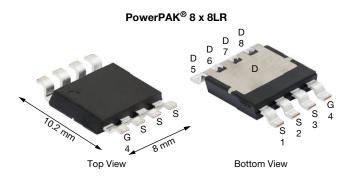




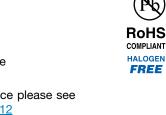
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

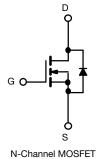


PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0009				
I _D (A)	575				
Configuration	Single				

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	PowerPAK 8 x 8LR
Lead (Pb)-free and halogen-free	SQJQ144AER (for detailed order number please see www.vishay.com/doc?79776)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	40	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current	T _C = 25 °C	1	575	
	T _C = 125 °C	- I _D	330	
Continuous source current (diode conduction)		I _S	545	Α
Pulsed drain current ^a		I _{DM}	1800	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	60	
Single pulse avalanche energy	L = 0.1 min	E _{AS}	180	mJ
Maximum power dissipation	T _C = 25 °C	Ъ	600	W
	T _C = 125 °C	P_{D}	200	VV
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) c		-	260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	44	°C/W	
Junction-to-case (drain)		R_{thJC}	0.25	C/VV	

Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \mu A$		40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		2	3	3.5		
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 40 V	=.	-	1		
	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	100	-	-	Α	
Drain-source on-state resistance ^a		V _{GS} = 10 V	I _D = 20 A	-	0.0007	0.0009	Ω	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0015		
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0019		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 60 A		-	160	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	=.	7220	9020	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		=	2290	2860		
Reverse transfer capacitance	C _{rss}			-	175	220		
Total gate charge ^c	Qg	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 30 A	-	116	145	nC	
Gate-source charge c	Q _{gs}			=	36	-		
Gate-drain charge ^c	Q _{gd}]		-	25	-		
Gate resistance	R_g	f = 1 MHz		0.9	1.6	2.6	Ω	
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V}, \text{ R}_L = 0.66 \Omega$ $I_D \cong 30 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	17	27	- ns	
Rise time ^c	t _r			-	27	41		
Turn-off delay time ^c	t _{d(off)}			=.	41	62		
Fall time ^c	t _f			=	18	27		
Source-Drain Diode Ratings and Cha	racteristics ^b							
Reverse recovery time	t _{rr}	V _{DD} = 32 V, I _{FM} = 15 A, di/dt = 100 A/μs			66		ns	
Reverse recovery charge	Q _{rr}			-	94	-	nC	
Reverse recovery current	I _{RM}			-	-	-3.6	Α	
Pulsed current ^a	I _{SM}			-	-	1600	Α	
Forward voltage	V _{SD}	I _F = 50 A, V _{GS} = 0			0.8	1.1	V	

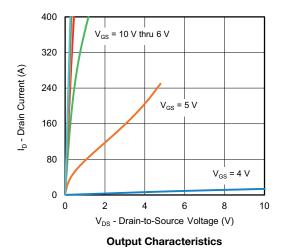
Notes

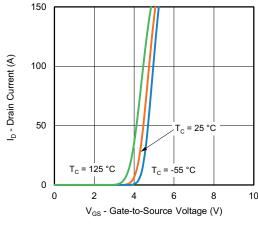
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

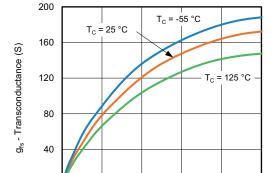
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)







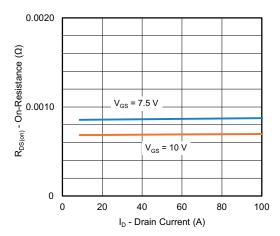
32

0

0

16

Transfer Characteristics



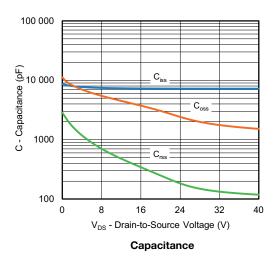
I_D - Drain Current (A) **Transconductance**

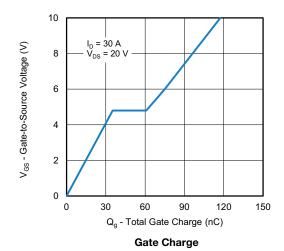
48

64

80

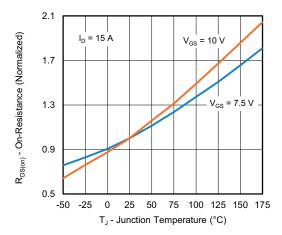
On-Resistance vs. Drain Current



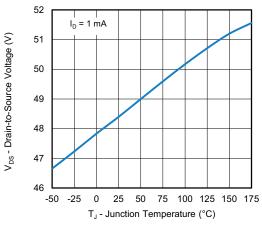




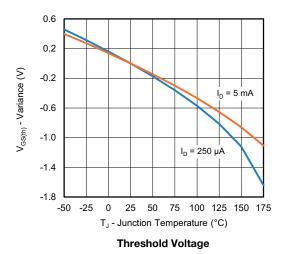
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

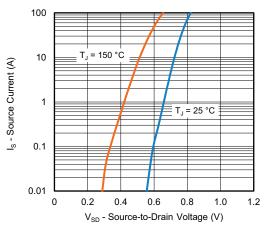


On-Resistance vs. Junction Temperature

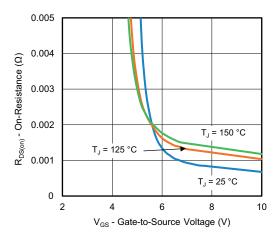


Drain Source Breakdown vs. Junction Temperature

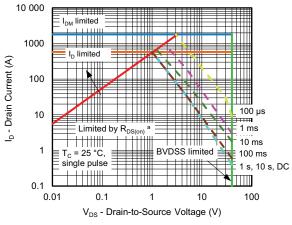




Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



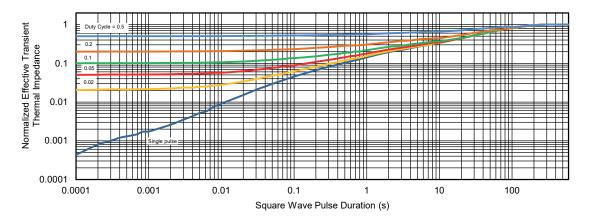
Safe Operating Area

Note

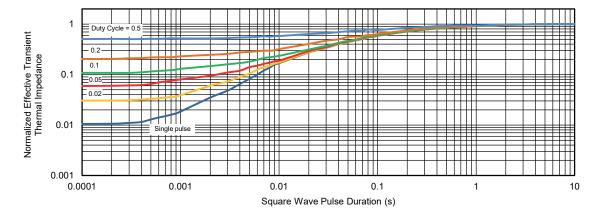
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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